Silicon Diode

BYV98

2kV/1A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

Fast soft-recovery rectifier BYV98

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Available in ammo-pack.

DESCRIPTION

Rugged glass SOD57 package, using a high temperature alloyed construction. This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

Fig.1 Simplified outline (SOD57) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RSM}	non-repetitive peak reverse voltage		–	2100	V
V_{RRM}	repetitive peak reverse voltage		–	2000	V
$I_{F(AV)}$	average forward current	T_{tp} = 55 °C; lead length = 10 mm see Fig. 2; averaged over any 20 ms period; see also Fig. 6	–	1.00	A
$I_{F(AV)}$	average forward current	T_{amb} = 60 °C; PCB mounting (see Fig.11); see Fig. 3; averaged over any 20 ms period; see also Fig. 6	–	0.43	A
I_{FRM}	repetitive peak forward current	T_{tp} = 55 °C; see Fig. 4	–	9.0	A
		T_{amb} = 60 °C; see Fig. 5	–	4.5	A
I_{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	–	15	A
T_{stg}	storage temperature		−65	+175	°C
T_j	junction temperature	see Fig.7	−65	+175	°C

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ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	I_F = 2 A; $T_j = T_{j\,max}$; see Fig. 8	–	–	2.2	V
		I_F = 2 A; see Fig. 8	–	–	2.4	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig. 9	–	–	5	µA
		$V_R = V_{RRMmax}$; T_j = 125 °C; see Fig. 9	–	–	50	µA
t_{rr}	reverse recovery time	when switched from I_F = 0.5 A to I_R = 1 A; measured at I_R = 0.25 A; see Fig. 12	–	–	300	ns
C_d	diode capacitance	f = 1 MHz; V_R = 0 V; see Fig 10	–	30	–	pF
$\left\|\frac{dI_R}{dt}\right\|$	maximum slope of reverse recovery current	when switched from I_F = 1 A to $V_R \geq 30$ V and $dI_F/dt = -1$ A/µs; see Fig.13	–	–	5	A/µs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	100	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 µm, see Fig.11. For more information please refer to the *'General Part of Handbook SC01'*.

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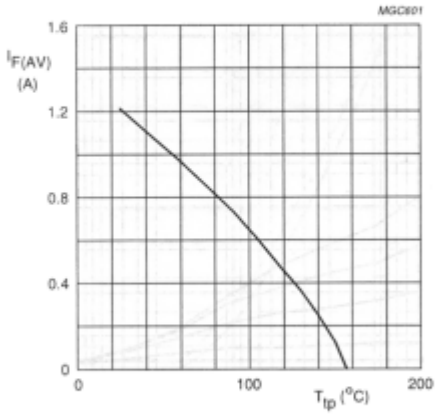
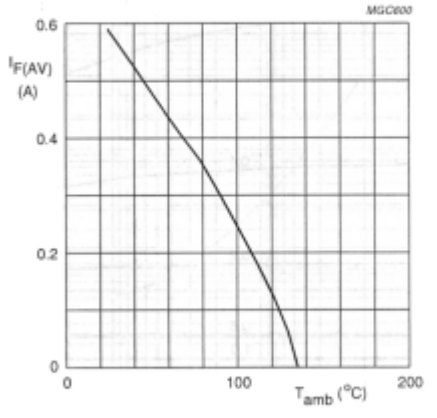
GRAPHICAL DATA



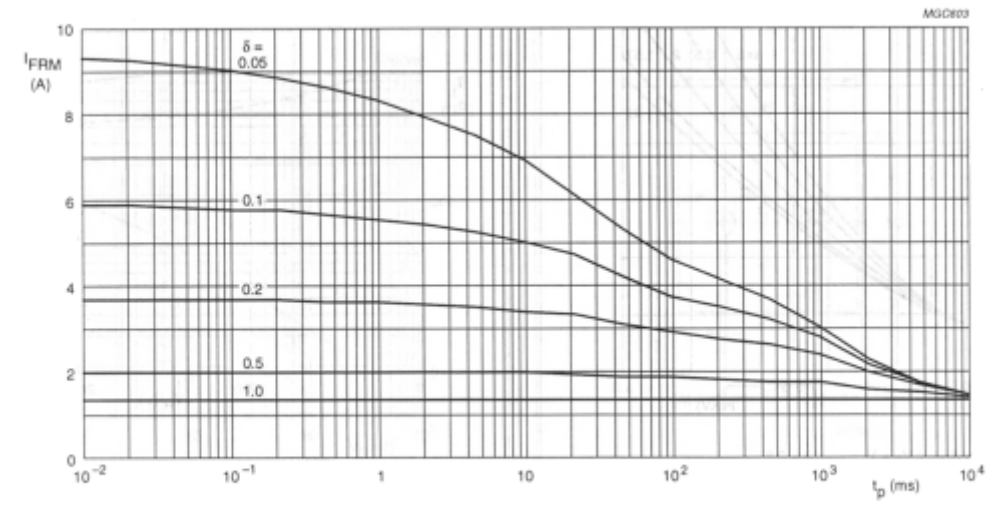
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Switched mode application.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.11.
Switched mode application.

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 46 K/W.
V_{RRMmax} during 1 − δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 2000 V.

Fig.4 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

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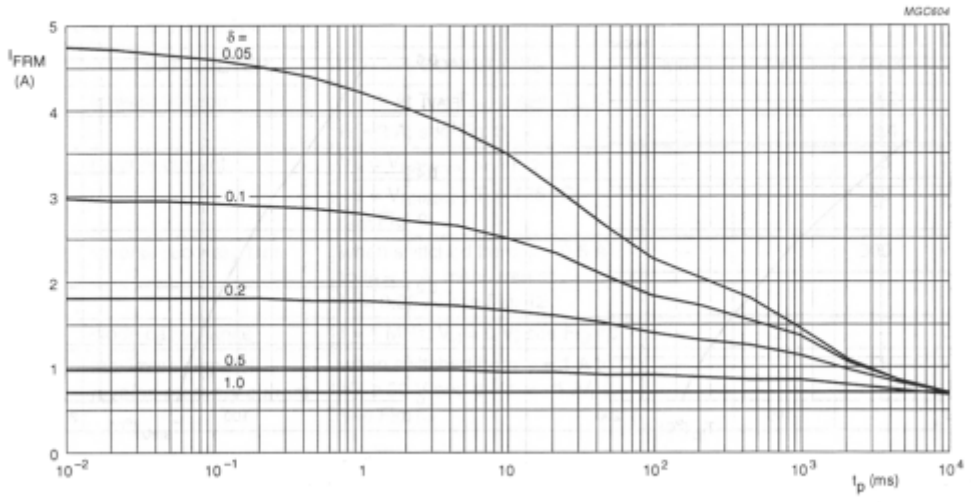
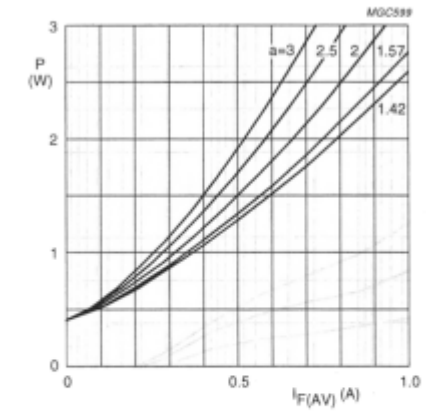


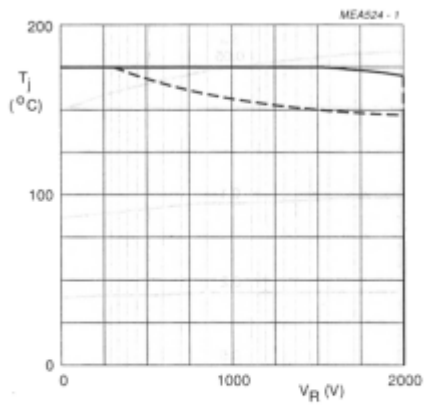
T_{amb} = 60 °C; $R_{th\ j-a}$ = 100 K/W.
V_{RRMmax} during 1 − δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 2000 V.

Fig.5 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.



$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.6 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



Solid line = V_{RRM}; δ = 0.1.
Dotted line = V_{RRM}; δ = 0.5.

Fig.7 Maximum permissible junction temperature as a function of reverse voltage.

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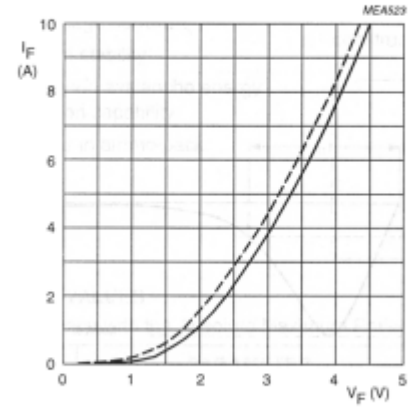
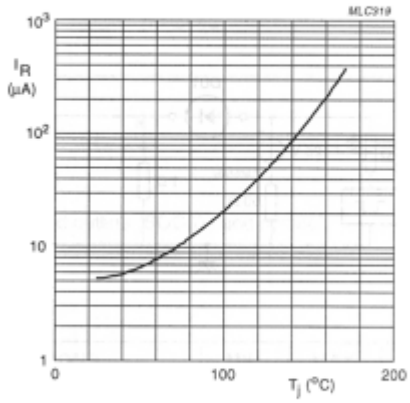


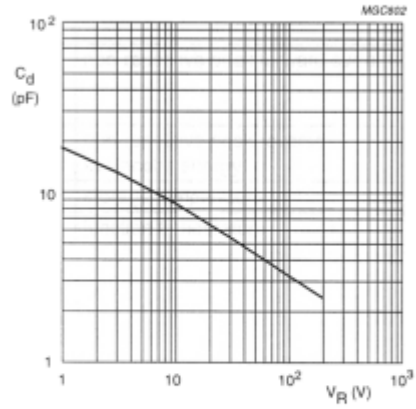
Dotted line: T_j = 175 °C.
Solid line: T_j = 25 °C.

Fig.8 Forward current as a function of forward voltage; maximum values.



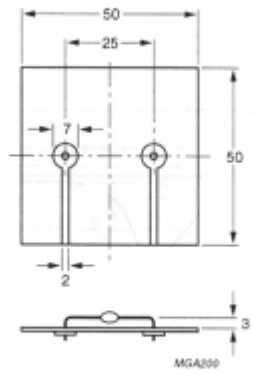
$V_R = V_{RRMmax}$.

Fig.9 Reverse current as a function of junction temperature; maximum values.



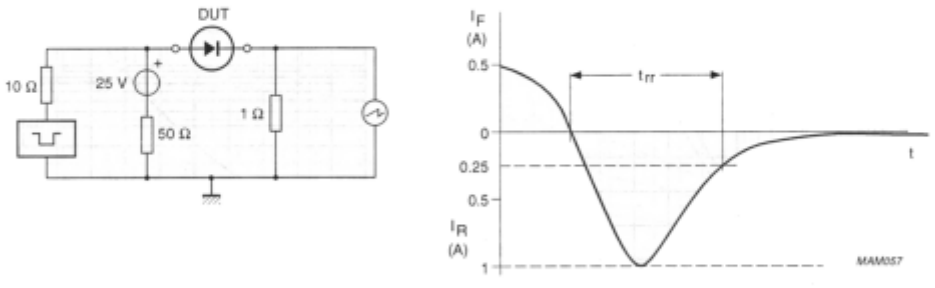
f = 1 MHz; T_j = 25 °C.

Fig.10 Diode capacitance as a function of reverse voltage; typical values.



Dimensions in mm.

Fig.11 Device mounted on a printed-circuit board.



Input impedance oscilloscope: 1 MΩ, 22 pF; $t_r \leq 7$ ns.
Source impedance: 50 Ω; $t_r \leq 15$ ns.

Fig.12 Test circuit and reverse recovery time waveform and definition.

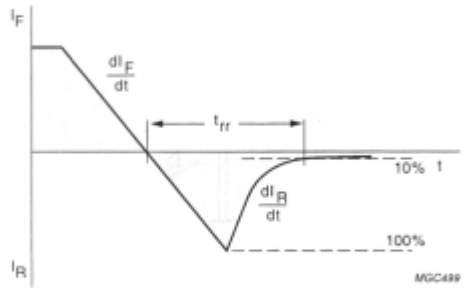


Fig.13 Reverse recovery definitions.